

μ PA2735GR

P-channel MOSFET

 $-30 \text{ V}, -16 \text{ A}, 5.0 \text{ m}\Omega$

R07DS0867EJ0100 Rev.1.00 Aug 28, 2012

Description

The μ PA2735GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} = -30 \text{ V } (T_A = 25^{\circ}\text{C})$
- Low on-state resistance
 - --- $R_{DS(on)}$ = 5.0 mΩ MAX. (V_{GS} = -10 V, I_D = -16 A)
- 4.5 V Gate-drive available
- Small and surface mount package (Power SOP8)
- Pb-free and Halogen free



Power SOP8

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2735GR-E1-AT	Pure Sn	Tape 2500 p/reel	Power SOP8
μ PA2735GR-E2-AT			0.08 g TYP.

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	∓20	V
Drain Current (DC)	I _{D(DC)}	∓16	Α
Drain Current (pulse) *1	I _{D(pulse)}	∓150	Α
Total Power Dissipation *2	P _{T1}	1.1	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	2.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	−55 to +150	°C
Single Avalanche Current *3	I _{AS}	16	А
Single Avalanche Energy *3	E _{AS}	25.6	mJ

Thermal Resistance

Channel to Ambient Thermal Resistance *2 R_{th(ch-A)} 114 °C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

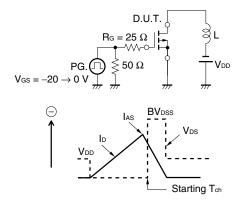
*3. Starting T_{ch} = 25°C, V_{DD} = -15 V, R_G = 25 Ω , V_{GS} = -20 \rightarrow 0 V, L = 100 μH

Electrical Characteristics (T_A = 25°C)

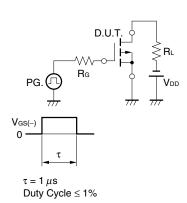
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓100	nA	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	-1.0		-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	10			S	$V_{DS} = -10 \text{ V}, I_{D} = -8.0 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		3.8	5.0	mΩ	$V_{GS} = -10 \text{ V}, I_D = -16 \text{ A}$
Resistance *1	R _{DS(on)2}		5.1	7.8	mΩ	$V_{GS} = -4.5 \text{ V}, I_{D} = -16 \text{ A}$
Input Capacitance	C _{iss}		6250		pF	$V_{DS} = -10 \text{ V},$
Output Capacitance	Coss		3900		pF	$V_{GS} = 0 V$,
Reverse Transfer Capacitance	C _{rss}		2850		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		35		ns	$V_{DD} = -15 \text{ V}, I_D = -8.0 \text{ A},$
Rise Time	t _r		85		ns	$V_{GS} = -10 \text{ V},$
Turn-off Delay Time	t _{d(off)}		300		ns	$R_G = 10 \Omega$
Fall Time	t _f		400		ns	
Total Gate Charge	Q_G		195		nC	$V_{DD} = -24 \text{ V},$
Gate to Source Charge	Q _{GS}		15		nC	$V_{GS} = -10 \text{ V},$
Gate to Drain Charge	Q_{GD}		100		nC	I _D = -16 A
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.82		V	I _F = 16 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		60		ns	$I_F = 16 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		88		nC	di/dt = 100 A/μs

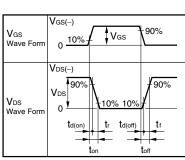
Note: *1. Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

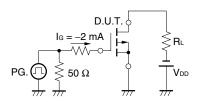


TEST CIRCUIT 2 SWITCHING TIME





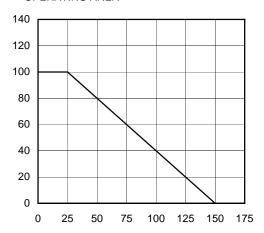
TEST CIRCUIT 3 GATE CHARGE



dT - Percentage of Rated Power - %

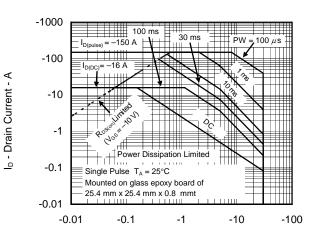
TYPICAL CHARACTERISTICS (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



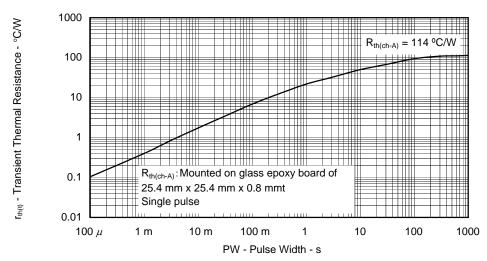
T_A - Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA

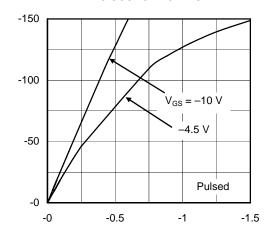


V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

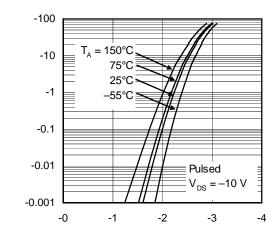


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS



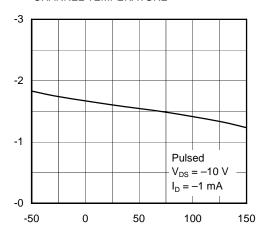
V_{GS} - Gate to Source Voltage - V

I_D - Drain Current - A

lo - Drain Current - A

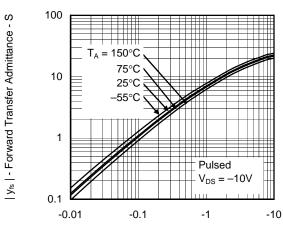
 $V_{\text{GS}(\text{off})}$ – Gate to Source Cut-off Voltage - V

GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



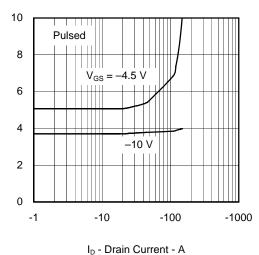
T_{ch} - Channel Temperature - °C

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

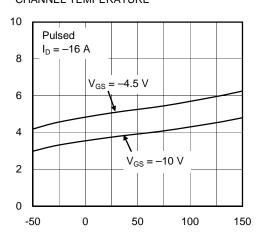


I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

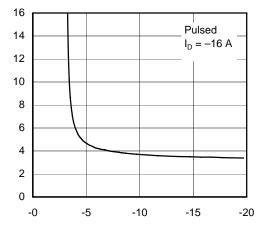


DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



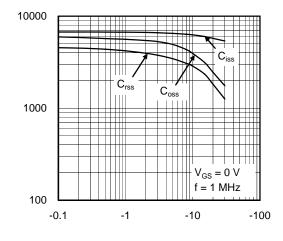
 T_{ch} - Channel Temperature - $^{\circ}C$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



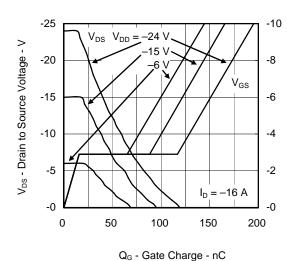
 V_{DS} - Drain to Source Voltage - V

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

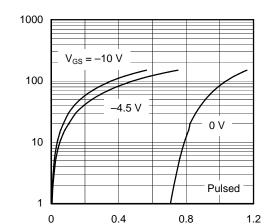
Ciss, Coss, Crss - Capacitance - pF

DYNAMIC INPUT/OUTPUT CHARACTERISTICS





I_F - Diode Forward Current - A

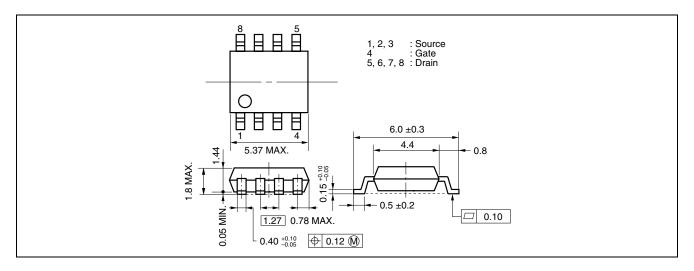


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

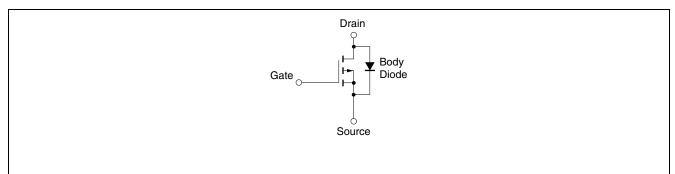
 $V_{F(S\text{-}D)}$ - Source to Drain Voltage - V

Package Drawings (Unit: mm)

Power SOP8



Equivalent Circuit



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Revision History

μ PA2735GR Data Sheet

		Description		
Rev.	Date	Page	e Summary	
1.00	Aug 28, 2012	_	First Edition Issued	

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Milliboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Ha Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 i. nunLu Haidian District. Beiiing 100083. P.R.China

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2868-9318, Fax: +852 2869-9022/9044

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

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